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R2A20101BM/NP

Monolithic Synchronous Step-Down DC/DC Converter

REJ03D0790-0300 Rev.3.00 May 14, 2008

Features

- Built-in low Ron power MOS FETs Pch Ron = 0.30 Ω (Typ), Nch Ron = 0.14 Ω (Typ)
- High switching frequency: 2 MHz (Max)
- Output current: 650 mA (Max)
- Output ON/OFF control
- Vout control
- Power good monitor
- Current share for redundant power supply operation
- Vout = 0.5 V to (VIN 0.5) V

Application

- POL (Point of Load) power supplies
- Power supply for microcomputer systems MCU-Core, I/O, Memory (DDR, SRAM, FLASH, HDD, etc.), FPGA, DSP, Graphic Processor
- Battery powered equipment systems Cellular phone (CDMA power amplifier, MCU, DSP, ASIC), PDA, Digital camera, Portable game, Handy terminal

Operating Circuit Example



Block Diagram



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

ltem	Symbol	Ratings	Unit	Note
Power supply voltage	VIN	6	V	1
ON/OFF, PWGD, EAO, VREF,	V _{MAX}	–0.3 to (V _{IN} + 0.3)	V	1
LX, CRFB, VFB terminal voltage				
PGND terminal voltage	V _{PGND}	-0.3 to +0.3	V	1
Operating ambient temperature	Topr(Ta)	-40 to +85	°C	
Junction temperature 1	Tjmax1	+125	°C	
Junction temperature 2	Tjmax2	+150	°C	2
Storage temperature	Tstg	-55 to +150	°C	

Notes: 1. Rated voltages are with reference to the AGND pin.

2. Operation by Tjmax2 is made within 24 hours through life.

Pin Arrangement



Pin Description

Pin No.			
R2A20101BM	R2A20101NP		
(CSP-15)	(QFN-24)	Pin Name	Pin Function
A1, A3, A5	15, 16, 17	PGND	Power ground
B2, B4	11, 20	LX	Inductor connection node
C1, C3, C5	10, 21	VIN	Power supply voltage input
D4	22	ON/OFF	Output on/off control input
D2	9	CRFB	CR feedback input
E5	23	PWGD	Power good monitor output
E1	8	VFB	Feedback voltage input
F4	2	EAO	Error amplifier output (for current share)
E3	5	VREF	Vout control voltage input
F2	4	AGND	Analog ground (IC chip ground voltage)

Note: Please apply solder to pins 1, 3, 6, 7, 12, 13, 14, 18, 19, and 24 even though they are NC pins. Solder on the underside pads improves heat-radiation characteristics.

Electrical Characteristics

$(Ta = 25^{\circ}C, Vin = 3.6 V, ON/\overline{OFF} = Vin, unless otherwise specified$									
ltem	Symbol	Min	Тур	Max	Unit	Test Conditions			
Input voltage range	Vin	2.5		5.5	V				
UVL threshold high	Vuvl-Hi	2.0	2.3	2.5	V	VFB = CRFB = GND,			
						Vin = rising			
UVL hysteresis	Vuvl-Hys	0.15	0.22	0.29	V				
Quiescent supply current	lss	20	45	80	μΑ				
Shutdown supply current	Ishdn	_	0.0	1.0	μΑ	$ON/\overline{OFF} = 0V$			
Reference voltage	Vref	0.485	0.500	0.515	V				
Vref line regulation	dVref/dVin	(-0.4)	0.1	(0)	%/V	Vin = 2.5 to 5.5V			
Vref temperature stability	dVref/dTa	_	(±100)	_	ppm/°C	Ta = -40 to +85°C			
VREF sink current	lvref-sink	1.3	3.7	8.0	μΑ	Vref = 2.5V			
VREF source current	Ivref-source	0.3	0.9	2.0	μΑ	Vref = 0V			
VFB leakage current	lleak-VFB	-1	0	+1	μΑ	$VFB = 1/2 \times Vin$			
Pch FET on resistance	Ron-Pch	_	0.30	0.50	Ω	VFB = CRFB = 0V,			
						ILX = -100mA			
Nch FET on resistance	Ron-Nch	-	0.14	0.25	Ω	VFB = CRFB = Vin,			
						ILX = 100mA			
Pch FET leakage current	lleak-Pch	_		1.0	μΑ	$ON/\overline{OFF} = 0V, LX = 0V$			
Nch FET leakage current	Ileak-Nch	_	_	1.0	μΑ	$ON/\overline{OFF} = 0V, LX = Vin$			
Peak current limit	Ipeak-Limit	0.7	_	_	Α				
ON/OFF threshold high	Von/off-Hi	1.0	1.45	1.85	V	ON/OFF = rising			
ON/OFF threshold low	Von/off-Lo	0.75	1.24	1.65	V	ON/OFF = falling			
ON/OFF leakage current	lleak-on/off	-1	0	+1	μΑ	ON/OFF = Vin			
ON/OFF input current	linput-on/off	_	1.4	5	μΑ	$ON/\overline{OFF} = 0.9V$			
Switching frequency	fsw	Adjustable by external Ccf1, Rcf1, Rcf2			Hz				
Soft start time	tss	56 × Rcf1/(Rcf1 + Rcf2) × Vout			μS				
Power good threshold	Vth-PGood	(–15)	-10	(–5)	%	Vref = 0.5V			
Power good VOL	Ipg-VOL	20	_	_	μΑ	PWGD = 0.2V, VFB = 0V			
Power good VOH	lpg-VOH	-10			μΑ	PWGD = 3.4V, VFB = 0.5V			
Output voltage load regulation	dVout/dlout		±0.7		%/A	$L = 2.2 \mu H$, Vout = 1.8V,			
						lout = 0 to 650mA			

Note: () is design spec.

Main Characteristics





Application Circuit Example

1. Current Share 1 (Redundant, Hot Swap type)



2. Current Share 2 (Accuracy type)



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3. Sequential Start-up



4. Tracking



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Package Dimensions





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RenesasTechnology Corp. sales Strategic Planning Div. Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan

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Renesas Technology America, Inc.

450 Holger Way, San Jose, CA 95134-1368, U.S.A Tel: <1> (408) 382-7500, Fax: <1> (408) 382-7501

Renesas Technology Europe Limited Dukes Meadow, Millboard Road, Bourne End, Buckinghamshire, SL8 5FH, U.K. Tel: <44> (1628) 585-100, Fax: <44> (1628) 585-900

Renesas Technology (Shanghai) Co., Ltd. Unit 204, 205, AZIACenter, No.1233 Lujiazui Ring Rd, Pudong District, Shanghai, China 200120 Tel: <86> (21) 5877-1818, Fax: <86> (21) 6887-7858/7898

Renesas Technology Hong Kong Ltd. 7th Floor, North Tower, World Finance Centre, Harbour City, Canton Road, Tsimshatsui, Kowloon, Hong Kong Tel: <852> 2265-6688, Fax: <852> 2377-3473

Renesas Technology Taiwan Co., Ltd. 10th Floor, No.99, Fushing North Road, Taipei, Taiwan Tel: <886> (2) 2715-2888, Fax: <886> (2) 3518-3399

Renesas Technology Singapore Pte. Ltd.

1 Harbour Front Avenue, #06-10, Keppel Bay Tower, Singapore 098632 Tel: <65> 6213-0200, Fax: <65> 6278-8001

Renesas Technology Korea Co., Ltd. Kukje Center Bldg. 18th Fl., 191, 2-ka, Hangang-ro, Yongsan-ku, Seoul 140-702, Korea Tel: <82> (2) 796-3115, Fax: <82> (2) 796-2145

Renesas Technology Malaysia Sdn. Bhd Unit 906, Block B, Menara Amcorp, Amcorp Trade Centre, No.18, Jln Persiaran Barat, 46050 Petaling Jaya, Selangor Darul Ehsan, Malaysia Tel: <603> 7955-9390, Fax: <603> 7955-9510

http://www.renesas.com